

AMENDMENTS TO THE CLAIMS:

1-14. (Canceled)

15. (Currently Amended) A light-emitting device using gallium nitride compound semiconductor ~~according to claim 1, further~~ comprising:

an emission layer with a multi quantum-well (MQW) structure, in which a barrier layer and a well layer are formed alternatively;

a substrate; and

a buffer layer formed on said substrate, wherein said barrier layer is made of

$\text{Al}_x\text{Ga}_{1-x}\text{N}$.

16. (Original) A light-emitting device using gallium nitride compound semiconductor according to claim 15, wherein said buffer layer is formed at a temperature of 1000°C to 1180°C.

17. (Original) A light-emitting device using gallium nitride compound semiconductor according to claim 15, wherein said buffer layer has a thickness of 0.01 μm to 3.2 μm .

18. (Currently Amended) A light-emitting device using gallium nitride compound semiconductor according to claim 15, wherein said buffer layer is formed by physical vapor deposit ~~such as~~ including any of sputtering, ion plating, and laser ablation, ECR, etc. ablation.

19. (Original) A light-emitting device using gallium nitride compound semiconductor according to claim 18, wherein said buffer layer has a thickness of 100 Å to 3000 Å.

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20. (Original) A light-emitting device using gallium nitride compound semiconductor according to claim 18, wherein said buffer layer is formed at a temperature of 200°C to 600°C.

21. (Currently Amended) A light-emitting device using gallium nitride compound semiconductor according to claim 18, wherein said buffer layer is treated by heat treatment at a temperature of 1000°C to 1250°C.

22. (Original) A light-emitting device using gallium nitride compound semiconductor according to claim 21, wherein said heat treatment is carried out in an atmosphere of H₂ and NH₃ gases.